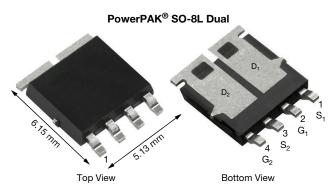
Vishay Siliconix

Automotive N- and P-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
	N-CHANNEL	P-CHANNEL			
V _{DS} (V)	40	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = \pm 10 \text{ V}$	0.0092	0.0270			
$R_{DS(on)}(\Omega)$ at $V_{GS} = \pm 4.5 \text{ V}$	0.0112	0.0435			
I _D (A)	30	-30			
Configuration	N- and	p-pair			

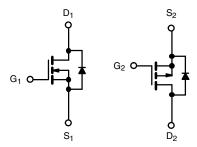
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



N-Channel MOSFET P-0

P-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ500AEP (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C =	= 25 °C, unless	otherwise n	oted)			
PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT		
Drain-source voltage		V _{DS}	40	-40	V	
Gate-source voltage		V_{GS}	± 20		V	
Continuous drain current ^a	T _C = 25 °C	1	30	-30		
Continuous drain current "	T _C = 125 °C	I _D	30	-18		
Continuous source current (diode conduction) a		I _S	30	-30	А	
Pulsed drain current ^b		I _{DM}	120	-120		
Single pulse avalanche current	Single pulse avalanche current		26.5	-25		
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	35	31	mJ	
Maximum power dissipation ^b	T _C = 25 °C	D	48	48	W	
maximum power dissipation ⁵	T _C = 125 °C	P_{D}	16	16	- VV	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175		°C	
Soldering recommendations (peak temperature) e, f			26	60	→ °C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Junction-to-ambient	PCB mount	R_{thJA}	85	85	°C/W
Junction-to-case (drain)		R_{thJC}	3.1	3.1	

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing
- e. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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PARAMETER	SYMBOL	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT	
Static		•							
During a superior beautiful and allower	.,,	V _{GS} =	N-Ch	40	-	-			
Drain-source breakdown voltage	V_{DS}	V _{GS} =	0 V, I _D = -250 μA	P-Ch	-40	-	-	.,	
Octor common through and control	.,	V _{DS} =	· V _{GS} , I _D = 250 μA	N-Ch	1.3	1.8	2.3	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	P-Ch	-1.5	-2	-2.5			
Octo common lockers		V 0VV : 20V		N-Ch	-	-	± 100	^	
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 40 V	N-Ch	-	-	1		
		V _{GS} = 0 V	V _{DS} = -40 V	P-Ch	-	-	-1		
Zava gota valtaga dvain suvvent		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	N-Ch	-	-	50		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	$V_{DS} = -40 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	P-Ch	-	-	-50	μA	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C		-	-	150]	
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 175 °C	P-Ch	-	-	-150		
On state duals assured a		V _{GS} = 10 V	$V_{DS} \ge 5 V$	N-Ch	25	-	-	Α	
On-state drain current a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le 5 V$	P-Ch	-25	-	-	^	
		V _{GS} = 10 V	I _D = 9.8 A	N-Ch	-	0.0077	0.0092		
		V _{GS} = -10 V	I _D = -6 A	P-Ch	-	0.0220	0.0270		
		V _{GS} = 10 V	I _D = 9.8 A, T _J = 125 °C	N-Ch	-	-	0.0138	Ω	
Duain accurac on atata registance 3		V _{GS} = -10 V	I _D = -6 A, T _J = 125 °C	P-Ch	-	-	0.0380		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 9.8 A, T _J = 175 °C	N-Ch	-	-	0.0170		
		V _{GS} = -10 V	I _D = -6 A, T _J = 175 °C	P-Ch	-	-	0.0460		
		V _{GS} = 4.5 V	I _D = 8.9 A	N-Ch	-	0.0094	0.0112		
		V _{GS} = -4.5 V	I _D = -4.7 A	P-Ch	-	0.0360	0.0435		
Farmer de transporter de la constant	_	V _{DS} =	$V_{DS} = 15 \text{ V}, I_D = 9.8 \text{ A}$		-	65	-		
Forward transconductance b	9 _{fs}	V _{DS} :	= -15 V, I _D = -6 A	P-Ch	-	16	-	S	
Dynamic ^b									
Innut conscitores		$V_{GS} = 0 V$	V _{DS} = 20 V, f = 1 MHz	N-Ch	-	1474	1843		
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = -20 V, f = 1 MHz	P-Ch	-	1302	1628		
0.15.15.55.51	0	$V_{GS} = 0 V$	V _{DS} = 20 V, f = 1 MHz	N-Ch	-	218	273	_	
Output capacitance	Coss	V _{GS} = 0 V	V _{DS} = -20 V, f = 1 MHz	P-Ch	-	222	278	pF	
Developed the market and a site of the sit	_	V _{GS} = 0 V	V _{DS} = 20 V, f = 1 MHz	N-Ch	-	89	111		
Reverse transfer capacitance	ansfer capacitance C_{rss} $V_{GS} = 0 V V$	V _{DS} = -20 V, f = 1 MHz	P-Ch	-	154	193			
Table and a discussion	_	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 10 \text{ A}$	N-Ch	-	25.5	38.3		
Total gate charge ^c	Q_g	V _{GS} = -10 V	$V_{DS} = -20 \text{ V}, I_{D} = -10 \text{ A}$	P-Ch	-	30.2	45		
	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 10 \text{ A}$	N-Ch	-	4.4	-	nC	
ate-source cnarge ^c		V _{GS} = -10 V	$V_{DS} = -20 \text{ V}, I_{D} = -10 \text{ A}$	P-Ch	-	4.1	-	1	
Gate-source charge c			i e e e e e e e e e e e e e e e e e e e	 		1		1	
		V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 10 \text{ A}$	N-Ch	-	4.3	-		
Gate-drain charge ^c	Q _{gd}	V _{GS} = 10 V V _{GS} = -10 V	$V_{DS} = 20 \text{ V}, I_D = 10 \text{ A}$ $V_{DS} = -20 \text{ V}, I_D = -10 \text{ A}$	N-Ch P-Ch	-	4.3 7.4	-		
	Q _{gd}						- - 2.1	Ω	



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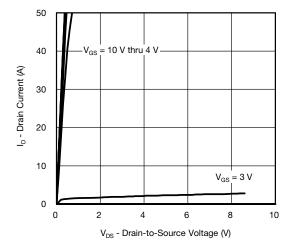
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT		
Dynamic ^b									
T. o. a. dala dia c	+	$\begin{aligned} V_{DD} &= 20 \text{ V, R}_L = 2 \Omega \\ I_D &\cong 10 \text{ A, V}_{GEN} = 10 \text{ V, R}_g = 1 \Omega \end{aligned}$	N-Ch	-	8	8 12			
Turn-on delay time ^c	t _{d(on)}	V_{DD} = -20 V, R_L = 2 Ω I_D \cong -10 A, V_{GEN} = -10 V, R_g = 1 Ω	N-Ch	-	7	11			
Rise time ^c	+	V_{DD} = 20 V, R_L = 2 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch	-	12	18			
nise unie °	t _r	V_{DD} = -20 V, R_L = 2 Ω I_D \cong -10 A, V_{GEN} = -10 V, R_g = 1 Ω	P-Ch	-	9	13	ne		
Turn-off delay time ^c	+	V_{DD} = 20 V, R_L = 2 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch	_	22	33	115		
rum-on delay time	t _{d(off)}	V_{DD} = -20 V, R_L = 2 Ω I_D \cong -10 A, V_{GEN} = -10 V, R_g = 1 Ω	P-Ch	ı	43	11 18 13 ns			
Fall time ^c	+.	$V_{DD} = 20 \text{ V, } R_L = 2 \Omega$ $I_D \cong 10 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$	N-Ch	ı	10	16			
ran ume -	me ^c t _f	V_{DD} = -20 V, R_L = 2 Ω I_D \cong -10 A, V_{GEN} = -10 V, R_g = 1 Ω	P-Ch	-	19	28			
Source-Drain Diode Ratings and Characteristics b									
Pulsed current ^a	I _{SM}		N-Ch	-	-	120	Δ		
i disca cuirent	ISM		P-Ch	-	-	-120	_ ^		
Forward voltage	Vor	I _S = 6.5 A	N-Ch	-	0.79	1.2	V		
Forward voltage V _{SD}		$I_{S} = -3.4 \text{ A}$	-	-0.78	-1.2	\ \			

Notes

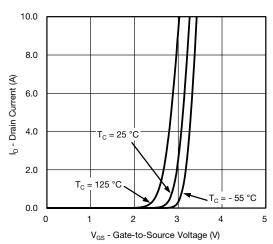
- g. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- h. Guaranteed by design, not subject to production testing
- i. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

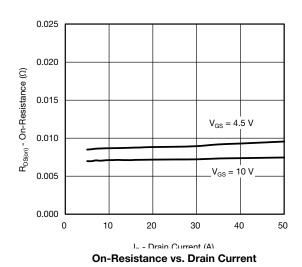


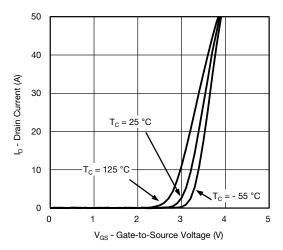


Output Characteristics

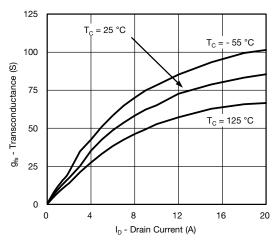


Transfer Characteristics

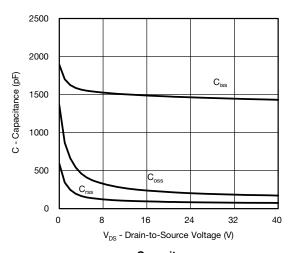




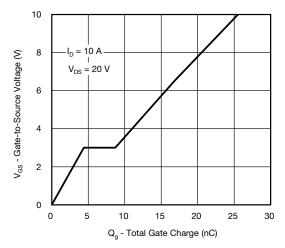
Transfer Characteristics



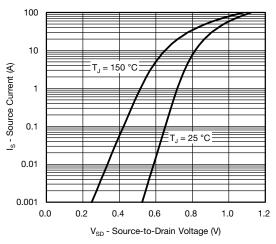
Transconductance



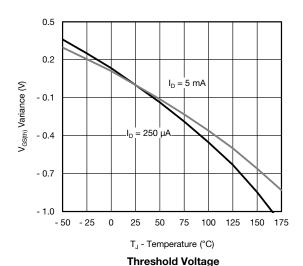


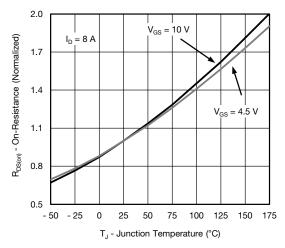


Gate Charge

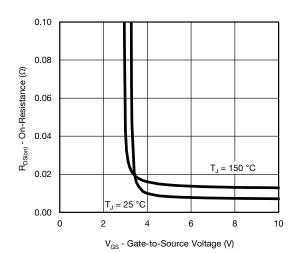


Source Drain Diode Forward Voltage

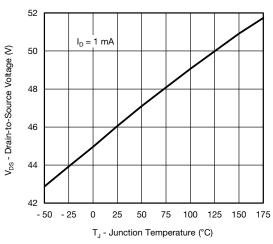




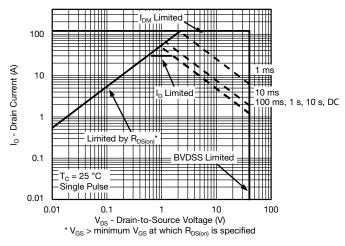
On-Resistance vs. Junction Temperature



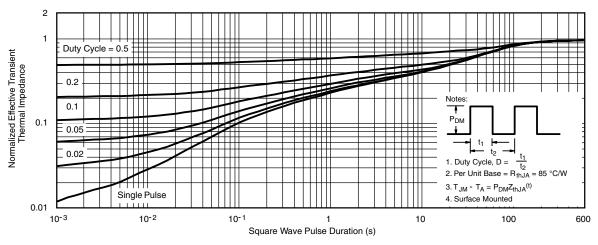
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

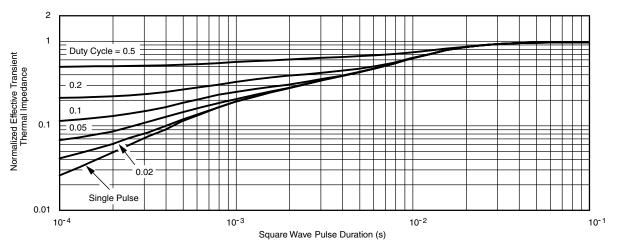


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient





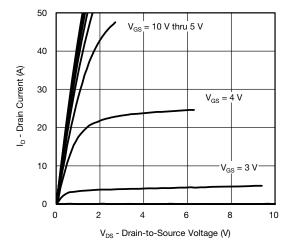
Normalized Thermal Transient Impedance, Junction-to-Case

Note

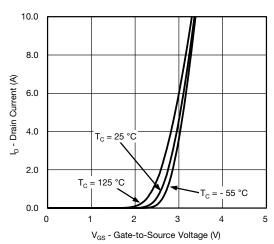
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

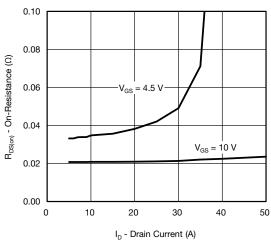




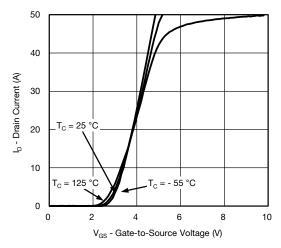
Output Characteristics



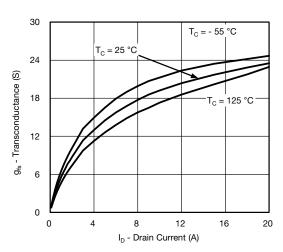
Transfer Characteristics



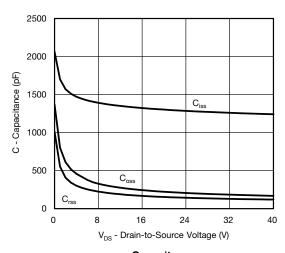
On-Resistance vs. Drain Current



Transfer Characteristics

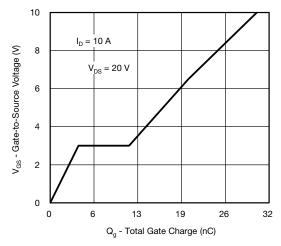


Transconductance

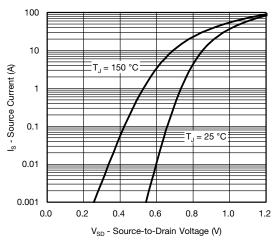


Capacitance

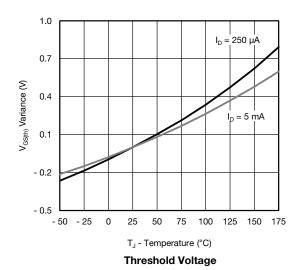




Gate Charge

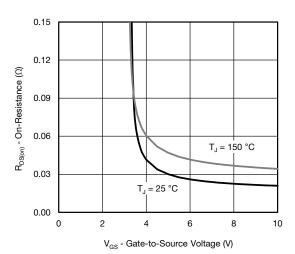


Source Drain Diode Forward Voltage

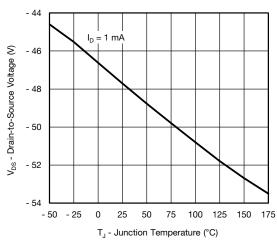


2.0 R_{DS(on)} - On-Resistance (Normalized) $I_D = 8 A$ $V_{GS} = 10 \text{ V}$ 1.7 1.4 $V_{GS} = 4.5 \text{ V}$ 1.1 0.8 0.5 - 25 0 25 125 - 50 50 75 100 150 175 T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

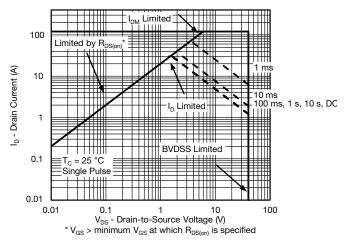


On-Resistance vs. Gate-to-Source Voltage

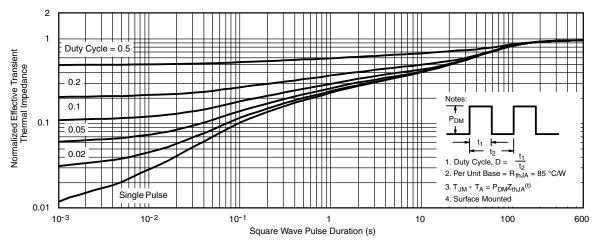


Drain Source Breakdown vs. Junction Temperature



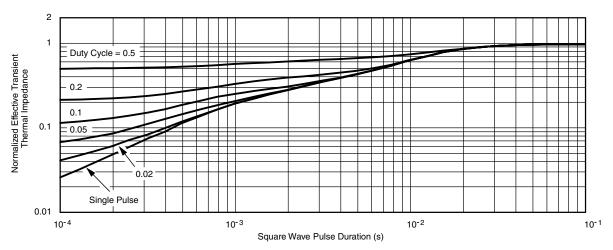


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient





Normalized Thermal Transient Impedance, Junction-to-Case

Note

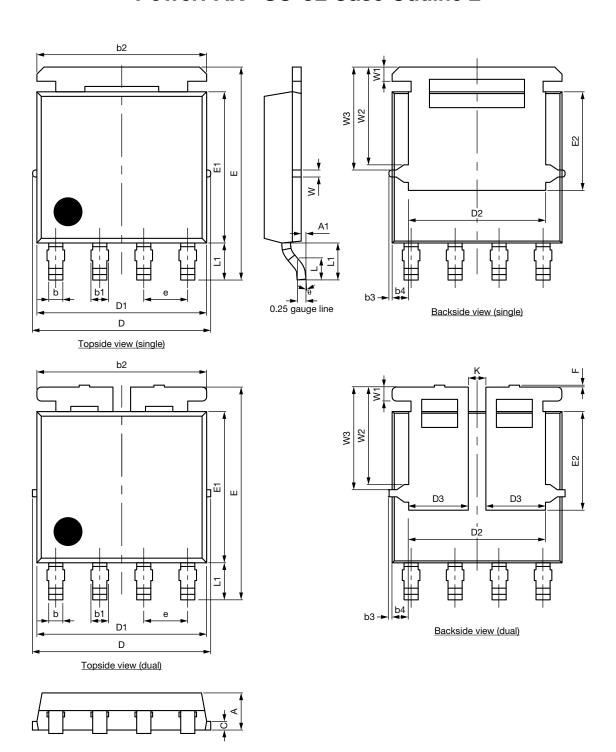
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62878.



PowerPAK® SO-8L Case Outline 2



Vishay Siliconix

DIM.		MILLIMETERS		INCHES			
Dilvi.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004	•	
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC			0.050 BSC		
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W		0.23			0.009		
W1	0.41			0.016			
W2		2.82			0.111		
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

ECN: C21-1498-Rev. C, 01-Nov-2021

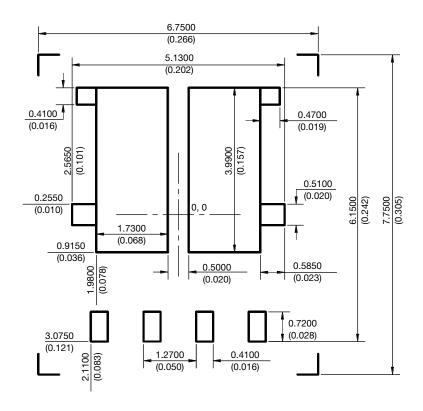
DWG: 6044

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)



Legal Disclaimer Notice

Vishay

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